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In memoriam

# Olga A. Golikova (1934–2002)[☆]

Prof. Dr. Olga A. Golikova passed away suddenly on March 9, 2002. Born on May 13, 1934, in Leningrad, USSR, Olga Golikova studied physics at the Leningrad Polytechnical Institute. Since 1958, she was with A.F. Ioffe Physico-Technical Institute, Russian Academy of Sciences (doctor degree in 1964, professor degree in 1971). She was the leader of a group studying the disordered semiconductors: refractory icosahedral boron-rich crystals and boron- and silicon-based films. The field of her scientific interest was semiconductor material science, including technological issues as well as investigations of thermoelectric and optoelectronic properties. She suggested the term “amorphous concept” to describe the icosahedral borides. Also note that the first devices with hydrogenated amorphous silicon were prepared in the USSR with her participation. Prof. O.A. Golikova was the author of approximately 200 publications and 8 USSR patents. She was the supervisor of 14 Ph.D. theses. Since 1987, she actively collaborated with world research centers in the USA, Europe (France, Germany, Belgium, Sweden), and Japan. The world has lost an outstanding scientist and bright person.

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